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b) Amendments to the Claims

Please cancel claim 3 and amend claims 1, 4, 12, 20 and 23 as follows. A detailed listing of the status of the claims that are or were in the application is provided.

--1. (Currently Amended) A method of manufacturing material comprising the steps of:

(A) contacting a solution containing a solvent, silicon and surfactant with a substrate ~~for controlling alignment of an opposing surface of an overcoated layer thereon~~ having alignment control ability to the surfactant; and

(B) drying said ~~coated~~ substrate to remove the solvent contained in said solution ~~and form a porous material~~ for forming a material having uniaxially aligned channel structures, wherein the channel structures comprise the surfactant and wherein the channel structures are substantially parallel to the substrate surface in which the surfactant is held within the porous material.

2. (Original) A method according to claim 1, wherein silicon is contained in said solution in a state of compound.

3. (Cancelled)

4. (Currently Amended) A method of manufacturing material, comprising the steps of:

coating a substrate having alignment control ability capable of
~~controlling alignment of an opposing surface of an overcoated layer thereon to a surfactant~~
with a ~~surfactant~~ solution containing silicon alkoxide and the surfactant; and
drying said coated substrate to form a ~~porous material with an~~
having uniaxially aligned channel structures, wherein the channel structures comprise the
surfactant and wherein the channel structures are substantially parallel to the substrate
surface in which the surfactant is held within the porous material.

5. (Previously Amended) A method according to claim 4, wherein the
step of coating the substrate is a step of selectively coating a desired portion of said
substrate with said solution in a desired pattern and, after the drying step, a patterned
mesostructured silica is formed.

6. (Previously Amended) A method according to claim 4 or 5, wherein
said substrate is a silicon single crystal substrate having (110) orientation.

7. (Original) A method according to claim 4 or 5, wherein said
substrate is a substrate whose surface is coated with a polymer compound film subjected to
a rubbing process.

8. (Original) A method according to claim 4 or 5, wherein said
substrate is a substrate whose surface is coated with a Langmuir-Blodgett film of polymer
compound.

9. (Previously Amended) A method according to any one of claims 4 or 5, wherein the substrate is coated with the surfactant solution by a pen lithography method.

10. (Previously Amended) A method according to any one of claims 4 or 5, wherein the substrate is coated with the surfactant solution by an ink jet method.

11. (Previously Amended) A method according to any one of claims 4 or 5, wherein the substrate is coated with the surfactant solution by a dip coating method.

12. (Currently Amended) A method of manufacturing material, comprising the steps of:

coating a substrate having alignment control ability ~~capable of controlling alignment of an opposing surface of an overcoated layer thereon to a surfactant~~ with a solution ~~of surfactant~~ containing a silicon ~~alkoxides~~ alkoxide and the surfactant;

drying said coated substrate to form a ~~porous~~ material having uniaxially aligned channel structures, wherein the channel structures comprise the surfactant and wherein the channel structures are substantially parallel to the substrate surface ~~in which the surfactant is held within the porous material~~; and, thereafter,

removing the surfactant.

13. (Previously Amended) A method according to claim 12, wherein said step of coating said substrate with said solution is a step of selectively coating a desired portion of said substrate with said solution in a desired pattern.

14. (Previously Amended) A method according to claim 12 or 13, wherein said substrate is a silicon single crystal substrate having (110) orientation.

15. (Original) A method according to claim 12 or 13, wherein said substrate is a substrate whose surface is coated with a polymer compound film subjected to a rubbing process.

16. (Original) A method according to any one of claims 12 or 13, wherein said substrate is a substrate whose surface is coated with a Langmuir-Blodgett film of polymer compound.

17. (Previously Amended) A method according to any one of claims 12 or 13, wherein said substrate is coated with said surfactant solution by a pen lithography method.

18. (Previously Amended) A method according to any one of claims 12 or 13, wherein said substrate is coated with said surfactant solution by an ink jet method.

19. (Previously Amended) A method according to any one of claims 12 or 13, wherein said substrate is coated with said surfactant solution by a dip coating method.

20. (Currently Amended) A method of manufacturing material, comprising the steps of:

(A) contacting a substrate having alignment control ability to a surfactant with attaching a solution containing a solvent, silicon and the surfactant to a substrate for controlling alignment of an opposing surface of an overcoated layer thereon; and

(B) drying said substrate ~~to which said solution is attached to remove the solvents contained in said solution and to~~ form a porous material having uniaxially aligned channel structures, wherein the channel structures comprise the surfactant and wherein the channel structures are substantially parallel to the substrate surface ~~in which the surfactant is held within the porous material attached to said substrate.~~

21. (Original) A method according to claim 20, wherein silicon is contained in said solution in the form of compound.

22. (Original) A method according to claim 20, wherein silicon is contained in said solution as silicon alkoxides.

23. (Currently Amended) A method of manufacturing material comprising the steps of:

(A) ~~contacting~~ coating a substrate having alignment control ability to a surfactant with a solution containing a solvent, silicon and the surfactant with a substrate; and

(B) drying said coated substrate ~~in contact with the solution to remove the solvent and to~~ form a porous material ~~which has~~ having uniaxially aligned channel structures, wherein the channel structures comprise the surfactant and wherein the channel structures are substantially parallel to the substrate surface and pores in which the surfactant is held.

24. (Previously Added) A method according to Claim 1, further comprising the step of removing said surfactant.--

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